AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings of claims in the application:

1 - 6. (Canceled)

7. (Currently Amended) A method of fabricating a liquid crystal display device wherein the device ~~devices~~ includes gate electrode lines, electrode links and electrode pads within a picture display part of a liquid crystal display panel, a gate insulating film of an inorganic material on a substrate provided with the gate electrode lines, links and pads, forming data electrode lines, electrode links and electrode pads on the gate insulating film, an organic protective film on the gate insulating film provided with the data electrode lines, links and pads, and a seal crossing the gate and data electrode links on the organic protective film, said method comprising:

removing the protective film and partially removing the gate insulating film to a predetermined thickness to define holes between the gate electrode links and the data electrode links; and

contacting the seal with the gate insulating film through the holes.

8. (Original) The method as claimed in claim 7, wherein the protective film and the gate insulating film are continuously removed by the dry etching technique.

9. (Original) The method as claimed in claim 8, further comprising:

forming a dummy pattern having said predetermined thickness before forming the gate insulating film at a predetermined area of the substrate prior to the dry etching work;

forming an etch point detection window at an area provided with the dummy pattern; and

terminating the etching process when the dummy pattern has been exposed from the etch point detection window during the dry etching.

10. (Original) The method as claimed in claim 7, wherein the holes are extended into the outside of an area occupied by the seal.

11. (Original) The method as claimed in claim 9, wherein the terminating the etching process step comprises:

monitoring reactive gas generation; and

terminating when the reactive gas is no longer being generated.

12 - 27. (Canceled)

28. (Original) A method to form a lower plate of a liquid crystal device, the method comprising:

forming a glass plate;

forming a gate insulating film over said lower glass plate such that at least a portion of said gate insulating film defines an adherence surface;

forming a protective film over said gate insulating film such that at least a portion of said adherence surface is exposed; and

forming a seal over said gate insulating film to make contact with said adherence surface.

29. (Original) The method of claim 28, wherein said adherence surface is defined on said glass plate by forming at least one hole in said gate insulating film to expose at least a portion of a surface of said glass plate.

30. (Original) The method of claim 28, further comprising:

forming a plurality of gate links between said lower glass plate and said gate insulation film.

31. (Original) The method of claim 30, wherein said adherence surface is disposed between at least two adjacent gate links.

32. (Original) The method of claim 28, further comprising:

forming a plurality of data links between said gate insulation film and said protective film.

33. (Original) The method of claim 32, wherein said adherence surface is disposed between at least two adjacent data links.

34. (Original) The method of claim 28, wherein said adherence surface extends beyond an edge of said seal.

35. (Original) The method of claim 28, wherein said adherence surface is inorganic.

36. (Original) A method to control a thickness of a gate insulation film remaining after etching, the method comprising:

forming an etch point detection window such that a dummy pattern of a predetermined thickness is formed below said gate insulation film;

simultaneously etching said etch point detection window and an actual pattern area; and

terminating the etching process when said dummy pattern becomes exposed.

37. (Original) The method of claim 36, wherein said terminating step comprises:

monitoring said etch point detection window for generation of reactive gases; and

terminating said etching process when said generation of reactive gases falls to or below a predetermined level.

38. (Previously Presented) The method of claim 36, wherein the etch point detection window is wider than the actual pattern area.

39. (Previously Presented) The method of claim 36, wherein the gate insulation film is part of a display device having a display part and a non-display part, and in the forming step, the etch point detection window is formed on the non-display part or on a pad portion of the display part.

40. (Previously Presented) The method of claim 36, wherein the predetermined thickness of the dummy pattern represents a desired thickness of the gate insulation film remaining after the etching, at where the etching occurred.

41. (Previously Presented) The method of claim 36, wherein the forming step includes:

forming a gate insulation film on a substrate;

forming an organic protective film on the gate insulation film; and

forming a photoresist pattern on the organic protective film to form the etch point detection window and the actual pattern area.

42. (Previously Presented) The method of claim 41, wherein the simultaneously etching step includes:

placing the substrate having the formed etch point detection window and the actual pattern area, in an etching chamber; and

injecting an etching gas into the etching chamber.

43. (Previously Presented) The method of claim 36, wherein, in the simultaneously etching step, an etching rate at the etch point detection window and an etching rate at the actual pattern area are the same.

44. (Previously Presented) The method of claim 36, wherein the actual pattern area includes at least one of the following:

an area between two adjacent data links; and

an area between two adjacent gate links.

45. (Previously Presented) The method of claim 37, wherein the reactive gases include non-volatile SiF_4 gas.